

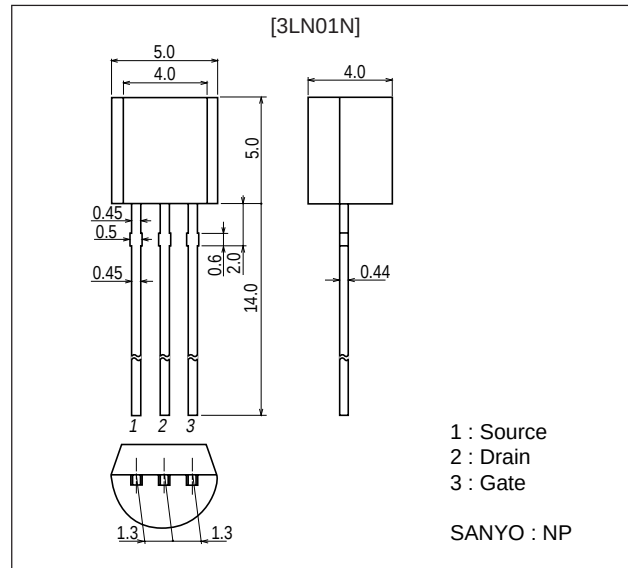
SANYO**Ultrahigh-Speed Switching Applications****Features**

- Low ON-resistance.
- Ultrahigh-speed switching.
- 2.5V drive.

Package Dimensions

unit : mm

2178

**Specifications****Absolute Maximum Ratings** at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		30	V
Gate-to-Source Voltage	V_{GSS}		± 10	V
Drain Current (DC)	I_D		0.15	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu\text{s}$, duty cycle $\leq 1\%$	0.6	A
Allowable Power Dissipation	P_D		0.4	W
Channel Temperature	T_{ch}		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$

Electrical Characteristics at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=1\text{mA}$, $V_{GS}=0$	30			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30\text{V}$, $V_{GS}=0$			10	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 8\text{V}$, $V_{DS}=0$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10\text{V}$, $I_D=100\mu\text{A}$	0.4		1.3	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10\text{V}$, $I_D=80\text{mA}$	0.15	0.22		S

Marking : YA

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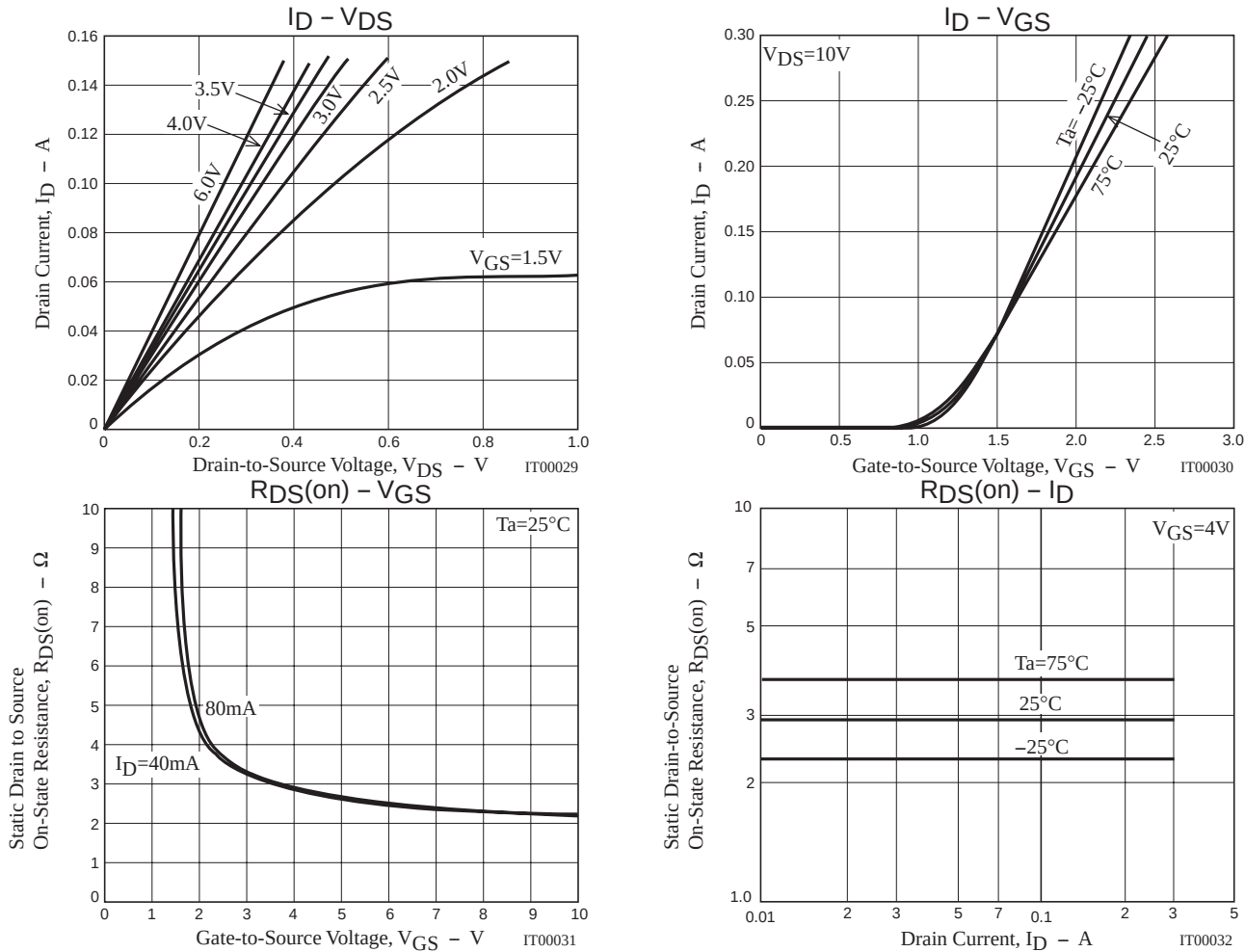
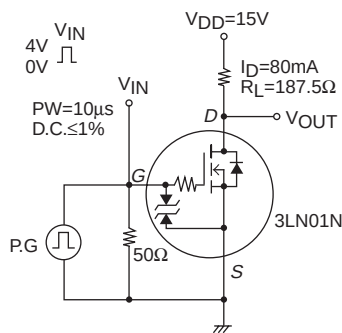
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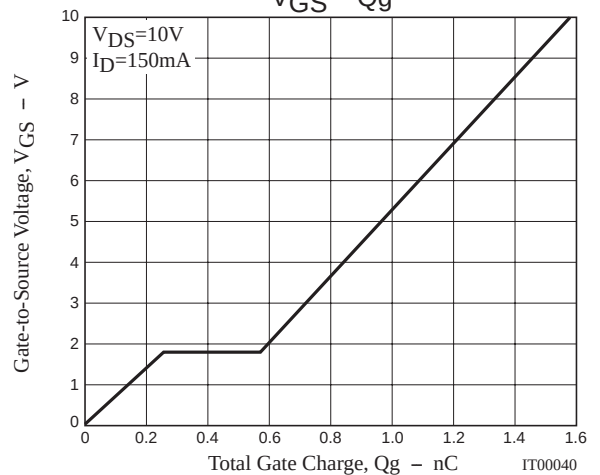
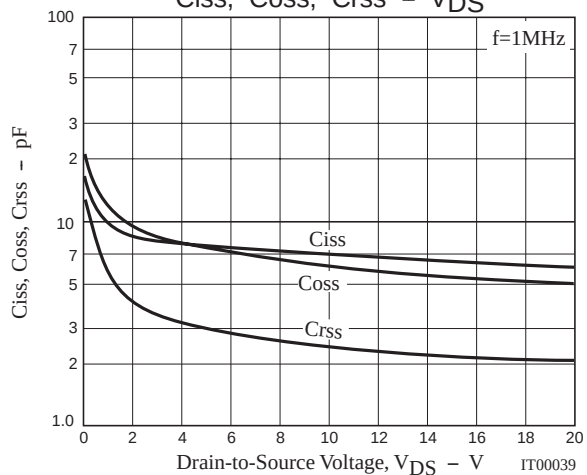
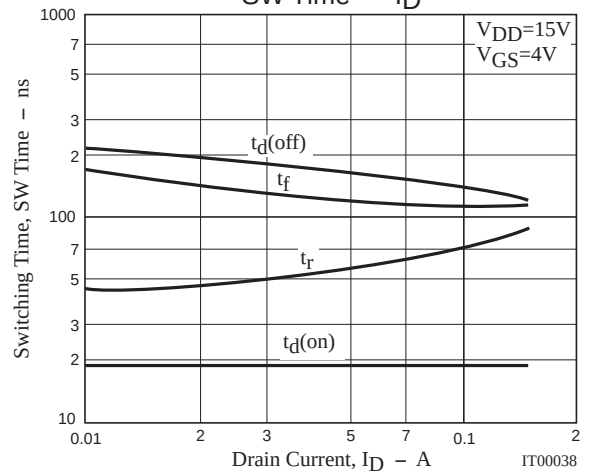
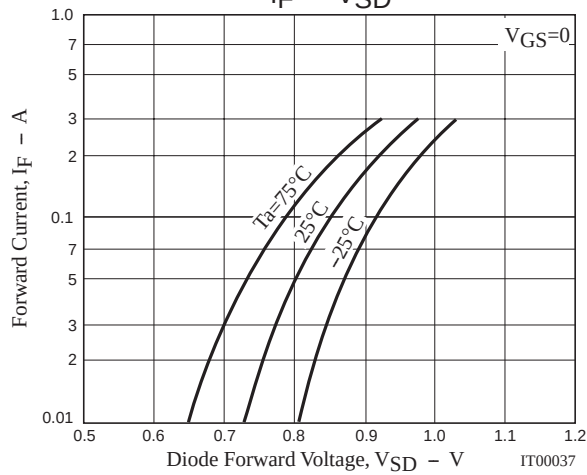
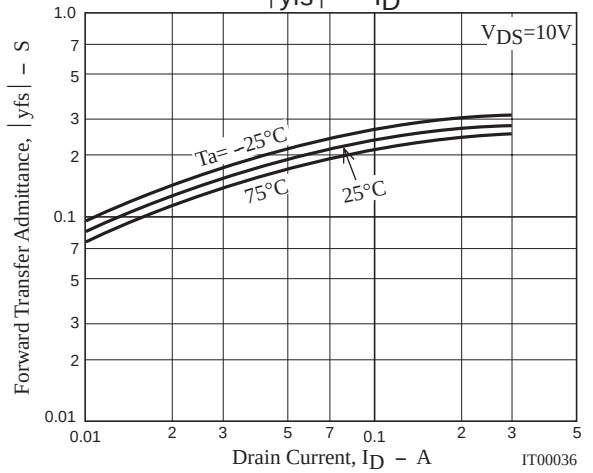
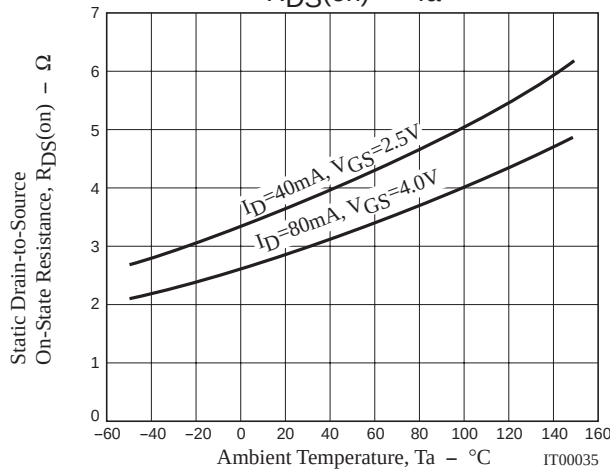
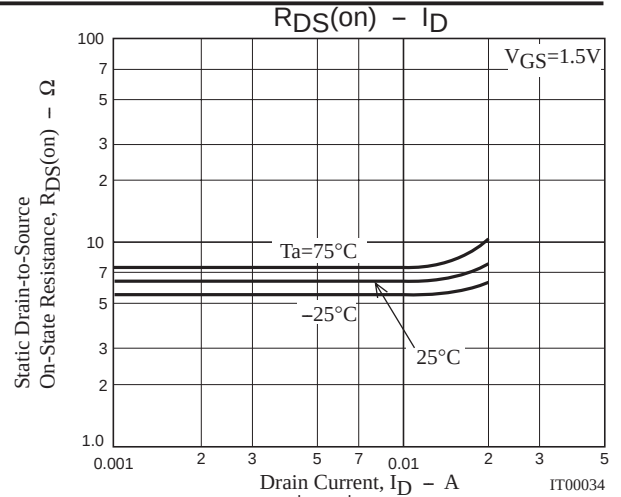
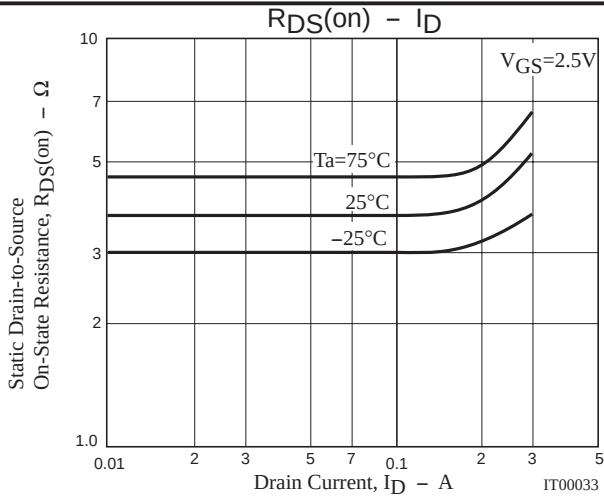
3LN01N

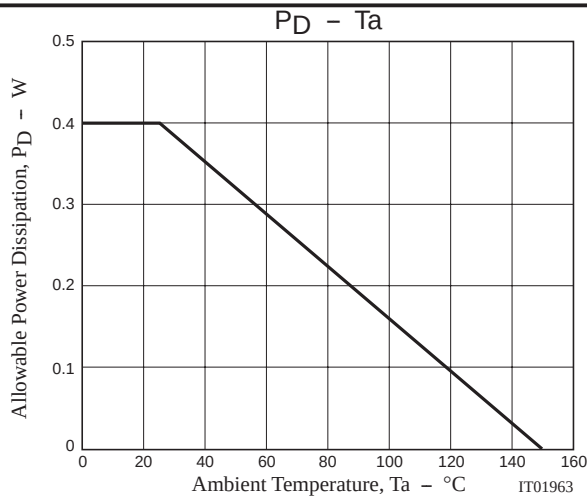
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=80\text{mA}$, $V_{GS}=4\text{V}$		2.9	3.7	Ω
	$R_{DS(on)2}$	$I_D=40\text{mA}$, $V_{GS}=2.5\text{V}$		3.7	5.2	Ω
	$R_{DS(on)3}$	$I_D=10\text{mA}$, $V_{GS}=1.5\text{V}$		6.4	12.8	Ω
Input Capacitance	C_{iss}	$V_{DS}=10\text{V}$, $f=1\text{MHz}$		7.0		pF
Output Capacitance	C_{oss}	$V_{DS}=10\text{V}$, $f=1\text{MHz}$		5.9		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=10\text{V}$, $f=1\text{MHz}$		2.3		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit		19		ns
Rise Time	t_r	See specified Test Circuit		65		ns
Turn-OFF Delay Time	$t_d(off)$	See specified Test Circuit		155		ns
Fall Time	t_f	See specified Test Circuit		120		ns
Total Gate Charge	Q_g	$V_{DS}=10\text{V}$, $V_{GS}=10\text{V}$, $I_D=150\text{mA}$		1.58		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS}=10\text{V}$, $V_{GS}=10\text{V}$, $I_D=150\text{mA}$		0.26		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS}=10\text{V}$, $V_{GS}=10\text{V}$, $I_D=150\text{mA}$		0.31		nC
Diode Forward Voltage	V_{SD}	$I_S=150\text{mA}$, $V_{GS}=0$		0.87	1.2	V

Switching Time Test Circuit







Note on usage : Since the 3LN01N is designed for high-speed switching applications, please avoid using this device in the vicinity of highly charged objects.

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